# Kazuya Terabe

#### List of Publications by Citations

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183 8,019 43 86 g-index

197 8,829 5 5.83 L-index

#	Paper	IF	Citations
183	Short-term plasticity and long-term potentiation mimicked in single inorganic synapses. <i>Nature Materials</i> , <b>2011</b> , 10, 591-5	27	1159
182	Quantized conductance atomic switch. <i>Nature</i> , <b>2005</b> , 433, 47-50	50.4	960
181	Atomic switch: atom/ion movement controlled devices for beyond von-neumann computers. <i>Advanced Materials</i> , <b>2012</b> , 24, 252-67	24	295
180	Learning abilities achieved by a single solid-state atomic switch. <i>Advanced Materials</i> , <b>2010</b> , 22, 1831-4	24	244
179	Forming and switching mechanisms of a cation-migration-based oxide resistive memory.  Nanotechnology, <b>2010</b> , 21, 425205	3.4	242
178	Effects of Moisture on the Switching Characteristics of Oxide-Based, Gapless-Type Atomic Switches. <i>Advanced Functional Materials</i> , <b>2012</b> , 22, 70-77	15.6	217
177	Electronic transport in Ta2O5 resistive switch. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 092110	3.4	196
176	Domain growth kinetics in lithium niobate single crystals studied by piezoresponse force microscopy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 012906	3.4	183
175	A nonvolatile programmable solid-electrolyte nanometer switch. <i>IEEE Journal of Solid-State Circuits</i> , <b>2005</b> , 40, 168-176	5.5	176
174	Synaptic Metaplasticity Realized in Oxide Memristive Devices. <i>Advanced Materials</i> , <b>2016</b> , 28, 377-84	24	164
173	Tbit/inch2 ferroelectric data storage based on scanning nonlinear dielectric microscopy. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4401-4403	3.4	161
172	On-demand nanodevice with electrical and neuromorphic multifunction realized by local ion migration. <i>ACS Nano</i> , <b>2012</b> , 6, 9515-21	16.7	153
171	Conductance quantization and synaptic behavior in a Ta2O5-based atomic switch. <i>Nanotechnology</i> , <b>2012</b> , 23, 435705	3.4	135
170	Controlling the Synaptic Plasticity of a Cu2S Gap-Type Atomic Switch. <i>Advanced Functional Materials</i> , <b>2012</b> , 22, 3606-3613	15.6	132
169	Microstructure and crystallization behaviour of TiO2 precursor prepared by the sol-gel method using metal alkoxide. <i>Journal of Materials Science</i> , <b>1994</b> , 29, 1617-1622	4.3	127
168	A Polymer-Electrolyte-Based Atomic Switch. Advanced Functional Materials, 2011, 21, 93-99	15.6	117
167	Diffusivity of Cu Ions in Solid Electrolyte and Its Effect on the Performance of Nanometer-Scale Switch. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 3283-3287	2.9	109

#### (1988-2003)

166	Microscale to nanoscale ferroelectric domain and surface engineering of a near-stoichiometric LiNbO3 crystal. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 433-435	3.4	104
165	Formation and disappearance of a nanoscale silver cluster realized by solid electrochemical reaction. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 10110	2.5	100
164	Synaptic plasticity and memory functions achieved in a WO3-x-based nanoionics device by using the principle of atomic switch operation. <i>Nanotechnology</i> , <b>2013</b> , 24, 384003	3.4	92
163	Rate-Limiting Processes Determining the Switching Time in a Ag2S Atomic Switch. <i>Journal of Physical Chemistry Letters</i> , <b>2010</b> , 1, 604-608	6.4	90
162	Resistance switching of an individual Ag2S/Ag nanowire heterostructure. <i>Nanotechnology</i> , <b>2007</b> , 18, 485202	3.4	72
161	In situ and non-volatile bandgap tuning of multilayer graphene oxide in an all-solid-state electric double-layer transistor. <i>Advanced Materials</i> , <b>2014</b> , 26, 1087-91	24	70
160	Switching kinetics of a Cu2S-based gap-type atomic switch. <i>Nanotechnology</i> , <b>2011</b> , 22, 235201	3.4	68
159	Optical Damage Resistance and Refractive Indices in Near-Stoichiometric MgO-Doped LiNbO3. Japanese Journal of Applied Physics, <b>2002</b> , 41, L49-L51	1.4	67
158	Temperature effects on the switching kinetics of a Cu-Ta2O5-based atomic switch. <i>Nanotechnology</i> , <b>2011</b> , 22, 254013	3.4	66
157	Structural studies of copper sulfide films: effect of ambient atmosphere. <i>Science and Technology of Advanced Materials</i> , <b>2008</b> , 9, 035011	7.1	65
156	In Situ Tuning of Magnetization and Magnetoresistance in Fe3O4 Thin Film Achieved with All-Solid-State Redox Device. <i>ACS Nano</i> , <b>2016</b> , 10, 1655-61	16.7	64
155	Ionic-electronic conductor nanostructures: template-confined growth and nonlinear electrical transport. <i>Small</i> , <b>2005</b> , 1, 971-5	11	59
154	Photocatalytic nanoparticle deposition on LiNbO3 nanodomain patterns via photovoltaic effect. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 044101	3.4	58
153	Effect of Ion Diffusion on Switching Voltage of Solid-Electrolyte Nanometer Switch. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 3666-3668	1.4	57
152	Fabrication of nanoscale gaps using a combination of self-assembled molecular and electron beam lithographic techniques. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 223111	3.4	56
151	Rearrangement of ferroelectric domain structure induced by chemical etching. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 022905	3.4	55
150	A general strategy toward transition metal carbide/carbon core/shell nanospheres and their application for supercapacitor electrode. <i>Carbon</i> , <b>2016</b> , 100, 590-599	10.4	54
149	Determination of Nonstoichiometry in YBa2Cu3O7-x. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, L1	79±1418°	1 53

148	Nanoionics Switching Devices: Atomic Switches MRS Bulletin, 2009, 34, 929-934	3.2	52
147	Polarization reversal in congruent and stoichiometric lithium tantalate. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 3146-3148	3.4	51
146	Ionic/electronic mixed conductor tip of a scanning tunneling microscope as a metal atom source for nanostructuring. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4009-4011	3.4	50
145	Domain Shape in Congruent and Stoichiometric Lithium Tantalate. Ferroelectrics, 2002, 269, 195-200	0.6	47
144	Imaging and engineering the nanoscale-domain structure of a Sr0.61Ba0.39Nb2O6 crystal using a scanning force microscope. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2044-2046	3.4	46
143	Effect of sulfurization conditions and post-deposition annealing treatment on structural and electrical properties of silver sulfide films. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 103501	2.5	45
142	Oxygen migration process in the interfaces during bipolar resistance switching behavior of WO3\( \mathbb{B}\)-based nanoionics devices. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 231603	3.4	43
141	AgI/Ag Heterojunction Nanowires: Facile Electrochemical Synthesis, Photoluminescence, and Enhanced Ionic Conductivity. <i>Advanced Functional Materials</i> , <b>2007</b> , 17, 1466-1472	15.6	43
140	Refractive Indices in Undoped and MgO-Doped Near-Stoichiometric LiTaO3 Crystals. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L465-L467	1.4	42
139	Down-scaling of resistive switching to nanoscale using porous anodic alumina membranes. <i>Journal of Materials Chemistry C</i> , <b>2014</b> , 2, 349-355	7.1	39
138	All-solid-state electric-double-layer transistor based on oxide ion migration in Gd-doped CeO2 on SrTiO3 single crystal. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 073110	3.4	39
137	Volatile/Nonvolatile Dual-Functional Atom Transistor. <i>Applied Physics Express</i> , <b>2011</b> , 4, 015204	2.4	39
136	Effect of sulfurization conditions on structural and electrical properties of copper sulfide films. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 073523	2.5	39
135	Memristive operations demonstrated by gap-type atomic switches. <i>Applied Physics A: Materials Science and Processing</i> , <b>2011</b> , 102, 811-815	2.6	38
134	Atomic switches: atomic-movement-controlled nanodevices for new types of computing. <i>Science and Technology of Advanced Materials</i> , <b>2011</b> , 12, 013003	7.1	37
133	Terabit inch Izferroelectric data storage using scanning nonlinear dielectric microscopy nanodomain engineering system. <i>Nanotechnology</i> , <b>2003</b> , 14, 637-642	3.4	37
132	Nanoscale domain switching at crystal surfaces of lithium niobate. <i>Chemical Physics Letters</i> , <b>2003</b> , 377, 475-480	2.5	35
131	In situ and nonvolatile photoluminescence tuning and nanodomain writing demonstrated by all-solid-state devices based on graphene oxide. <i>ACS Nano</i> , <b>2015</b> , 9, 2102-10	16.7	33

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130	Switching Property of Atomic Switch Controlled by Solid Electrochemical Reaction. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L364-L366	1.4	32	
129	Surface potential imaging of nanoscale LiNbO3 domains investigated by electrostatic force microscopy. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 132905	3.4	32	
128	Control of local ion transport to create unique functional nanodevices based on ionic conductors. <i>Science and Technology of Advanced Materials</i> , <b>2007</b> , 8, 536-542	7.1	31	
127	Effect of Ionic Conductivity on Response Speed of SrTiO3-Based All-Solid-State Electric-Double-Layer Transistor. <i>ACS Applied Materials &amp; Double State State</i>	9.5	30	
126	I-V characteristics of single electron tunneling from symmetric and asymmetric double-barrier tunneling junctions. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 223112	3.4	30	
125	High-Temperature Resistivity Measurements of YBa2Cu3O7-x. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, L220-L222	1.4	28	
124	Solid-Electrolyte Nanometer Switch. <i>IEICE Transactions on Electronics</i> , <b>2006</b> , E89-C, 1492-1498	0.4	28	
123	Nanoscale chemical etching of near-stoichiometric lithium tantalate. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 064308	2.5	27	
122	Flexible resistive switching memory using inkjet printing of a solid polymer electrolyte. <i>AIP Advances</i> , <b>2012</b> , 2, 022144	1.5	26	
121	Thermal stability of LiTaO3 domains engineered by scanning force microscopy. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 142906	3.4	25	
120	Shapes of isolated domains and field induced evolution of regular and random 2D domain structures in LiNbO3 and LiTaO3. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2005</b> , 120, 109-113	3.1	25	
119	Origin of green emission from ZnS nanobelts as revealed by scanning near-field optical microscopy. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 091908	3.4	24	
118	Formation of Metastable Silver Nanowires of Hexagonal Structure and Their Structural Transformation under Electron Beam Irradiation. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 6046-60	)4 <sup>1</sup> 8 <sup>4</sup>	24	
117	Size-dependent single electron tunneling effect in Au nanoparticles. Surface Science, 2007, 601, 3907-3	91.8	23	
116	Self-Organization in LiNbO3 and LiTaO3: Formation of Micro- and Nano-Scale Domain Patterns. <i>Ferroelectrics</i> , <b>2004</b> , 304, 111-116	0.6	23	
115	Resistance Switching in Anodic Oxidized Amorphous TiO2Films. <i>Applied Physics Express</i> , <b>2008</b> , 1, 064002	2 2.4	22	
114	Near-Stoichiometric LiTaO 3 for Bulk Quasi-Phase-Matched Devices. Ferroelectrics, 2002, 273, 199-204	0.6	22	
113	Operating mechanism and resistive switching characteristics of two- and three-terminal atomic switches using a thin metal oxide layer. <i>Journal of Electroceramics</i> , <b>2017</b> , 39, 143-156	1.5	21	

112	Mechanical twinning in stoichiometric lithium niobate single crystal. <i>Journal of Crystal Growth</i> , <b>1997</b> , 180, 101-104	1.6	21
111	Modulation of superconducting critical temperature in niobium film by using all-solid-state electric-double-layer transistor. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 013104	3.4	20
110	Micro x-ray photoemission and Raman spectroscopic studies on bandgap tuning of graphene oxide achieved by solid state ionics device. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 183101	3.4	20
109	Volatile and nonvolatile selective switching of a photo-assisted initialized atomic switch. <i>Nanotechnology</i> , <b>2013</b> , 24, 384006	3.4	20
108	Material dependence of switching speed of atomic switches made from silver sulfide and from copper sulfide. <i>Journal of Physics: Conference Series</i> , <b>2007</b> , 61, 1157-1161	0.3	20
107	Anomalous phase transition and ionic conductivity of AgI nanowire grown using porous alumina template. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 124308	2.5	20
106	Atomic Layer Deposition of a Magnesium Phosphate Solid Electrolyte. <i>Chemistry of Materials</i> , <b>2019</b> , 31, 5566-5575	9.6	19
105	A Ta2O5 solid-electrolyte switch with improved reliability <b>2007</b> ,		19
104	Domain patterning in LiNbO3 and LiTaO3 by focused electron beam. <i>Journal of Crystal Growth</i> , <b>2006</b> , 292, 324-327	1.6	19
103	Formation and crystallization of beta-alumina from precursor prepared by sol-gel method using metal alkoxides. <i>Solid State Ionics</i> , <b>1987</b> , 25, 171-176	3.3	19
102	Ionic decision-maker created as novel, solid-state devices. Science Advances, 2018, 4, eaau2057	14.3	19
101	Electron-Beam Domain Writing in Stoichiometric LiTaO3Single Crystal by Utilizing Resist Layer. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L399-L402	1.4	18
100	Nano-Domain Engineering in LiNbO3by Focused Ion Beam. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L1550-L1552	1.4	17
99	Nanoionic devices enabling a multitude of new features. <i>Nanoscale</i> , <b>2016</b> , 8, 13873-9	7.7	17
98	Direct observation of redox state modulation at carbon/amorphous tantalum oxide thin film hetero-interface probed by means of in situ hard X-ray photoemission spectroscopy. <i>Solid State Ionics</i> , <b>2013</b> , 253, 110-118	3.3	16
97	Room temperature redox reaction by oxide ion migration at carbon/Gd-doped CeO heterointerface probed by an hard x-ray photoemission and soft x-ray absorption spectroscopies. <i>Science and Technology of Advanced Materials</i> , <b>2013</b> , 14, 045001	7.1	16
96	Template synthesis of M/M2S (M = Ag, Cu) hetero-nanowires by electrochemical technique. <i>Solid State Ionics</i> , <b>2006</b> , 177, 2527-2531	3.3	16
95	Size-Controlled AgI/Ag Heteronanowires in Highly Ordered Alumina Membranes: Superionic Phase Stabilization and Conductivity. <i>Nano Letters</i> , <b>2015</b> , 15, 5161-7	11.5	15

## (-2005)

94	A comparative study on the domain switching characteristics of near stoichiometric lithium niobate and lithium tantalate single crystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2005</b> , 120, 125-129	3.1	15	
93	Decision maker based on atomic switches. AIMS Materials Science, 2016, 3, 245-259	1.9	15	
92	Theoretical investigation of kinetics of a Cu2S-based gap-type atomic switch. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 233501	3.4	14	
91	Transmission electron microscopy observation and optical property of sol-gel derived LiNbO3 films. Journal of Materials Research, <b>1996</b> , 11, 3152-3157	2.5	14	
90	Defect chemical study of Nd2⊠CexCuO4□ <i>Solid State Ionics</i> , <b>1991</b> , 49, 63-70	3.3	14	
89	A nonvolatile programmable solid electrolyte nanometer switch		13	
88	Ferroelectric Nanodomain Properties in Near-Stoichiometric and Congruent LiNbO3Crystals Investigated by Scanning Force Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 7012-7014	1.4	13	
87	Phase Relation of ZrO2-YO1.5-TiO2 Ceramics Prepared by Sol-Gel Method. <i>Journal of the Ceramic Society of Japan</i> , <b>1998</b> , 106, 860-866		12	
86	Effect of substrates on the crystallinity and morphology of sol-gel-derived epitaxial LiNbO3 films. Journal of Materials Research, <b>1995</b> , 10, 1779-1783	2.5	12	
85	Nanoionic devices: Interface nanoarchitechtonics for physical property tuning and enhancement. Japanese Journal of Applied Physics, <b>2016</b> , 55, 1102A4	1.4	12	
84	Significant roles of the polymer matrix in the resistive switching behavior of polymer-based atomic switches. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 445301	3	11	
83	Magnetic Control of Magneto-Electrochemical Cell and Electric Double Layer Transistor. <i>Scientific Reports</i> , <b>2017</b> , 7, 10534	4.9	11	
82	Effect of nonstoichiometric defects on antiparallel domain formation in LiNbO3. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 232913	3.4	11	
81	High responsivity in MoS2 phototransistors based on charge trapping HfO2 dielectrics. <i>Communications Materials</i> , <b>2020</b> , 1,	6	11	
80	Structure analysis of stoichiometric LiNbO 3 (0 0 0 1) surfaces using low-energy neutral scattering spectroscopy. <i>Surface Science</i> , <b>2003</b> , 538, L500-L504	1.8	10	
79	Optical waveguide properties of single indium oxide nanofibers. <i>Journal of Optics</i> , <b>2008</b> , 10, 055201		9	
78	SIMS-depth profile and microstructure studies of Ti-diffused Mg-doped near-stoichiometric lithium niobate waveguide. <i>Journal of Crystal Growth</i> , <b>2006</b> , 287, 472-477	1.6	9	
77	Three terminal solid-electrolyte nanometer switch		9	

76	Preparation of layered Si materials as anode for lithium-ion batteries. <i>Chemical Physics Letters</i> , <b>2019</b> , 730, 198-205	2.5	8
75	Stability of engineered domains in ferroelectric LiNbO3and LiTaO3crystals. <i>Physica Scripta</i> , <b>2007</b> , T129, 103-107	2.6	8
74	Nanoscale Domain Engineering of a Sr 0.61 Ba 0.39 Nb 2 O 6 Single Crystal Using a Scanning Force Microscope. <i>Ferroelectrics</i> , <b>2003</b> , 292, 83-89	0.6	8
73	Fabrication of graphene/MoS2 alternately stacked structure for enhanced lithium storage. <i>Materials Chemistry and Physics</i> , <b>2020</b> , 239, 121987	4.4	8
72	Theoretical modeling of electrode impedance for an oxygen ion conductor and metallic electrode system based on the interfacial conductivity theory. Part II: Case of the limiting process by non-steady-state surface diffusion. <i>Solid State Ionics</i> , <b>2013</b> , 249-250, 78-85	3.3	7
71	In Situ Hard X-ray Photoelectron Spectroscopy of Space Charge Layer in a ZnO-Based All-Solid-State Electric Double-Layer Transistor. <i>Journal of Physical Chemistry C</i> , <b>2019</b> , 123, 10487-10493	3.8	6
70	Electrical-pulse-induced resistivity modulation in Pt/TiO2  Pt multilayer device related to nanoionics-based neuromorphic function. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 06GH01	1.4	6
69	Stabilization of periodically poled domain structures in a quasiphase-matching device using near-stoichiometric LiTaO3. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 014101	2.5	6
68	Nano-Sized Inverted Domain Formation in Stoichiometric LiTaO 3 Single Crystal Using Scanning Nonlinear Dielectric Microscopy. <i>Integrated Ferroelectrics</i> , <b>2002</b> , 49, 203-209	0.8	6
67	Metastable Phase Relationship in the ZrO2-YO1.5, ZrO2-TiO2 and YO1.5-TiO2 Systems. <i>Journal of the Ceramic Society of Japan</i> , <b>1998</b> , 106, 782-786		6
66	Characterization of sodium \$beta;-alumina prepared by sol-gel method. <i>Solid State Ionics</i> , <b>1990</b> , 40-41, 111-114	3.3	6
65	An ESR Study of YBa2Cu3O7-xand Y2BaCuO5with Oxygen Deficiencies. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, L2336-L2338	1.4	6
64	Comparison of subthreshold swing in SrTiO3-based all-solid-state electric-double-layer transistors with Li4SiO4or Y-stabilized-ZrO2solid electrolyte. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 06GJ03	3 <sup>1.4</sup>	6
63	Correlated Metal SrVO3 Based All-Solid-State Redox Transistors Achieved by Li+ or H+ Transport. Journal of the Physical Society of Japan, <b>2018</b> , 87, 034802	1.5	5
62	Revival of "dead" memristive devices: case of WO3-x. <i>Physical Chemistry Chemical Physics</i> , <b>2016</b> , 18, 139	2366	5
61	Investigation of Ag and Cu Filament Formation Inside the Metal Sulfide Layer of an Atomic Switch Based on Point-Contact Spectroscopy. <i>ACS Applied Materials &amp; Distributed &amp; Distributed &amp; Distributed &amp; Distributed &amp; Distrib</i>	9.5	5
60	Quantized Conductance and Neuromorphic Behavior of a Gapless-Type Ag-Ta2O5 Atomic Switch. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1562, 1		5
59	Temperature effects on the switching kinetics of a Cu-Ta2O5-based atomic switch. <i>Nanotechnology</i> , <b>2011</b> , 22, 379502	3.4	5

## (2021-2006)

58	Domain and Surface Structuring of LiNbO3 Single Crystal by Scanning Force Microscopy. <i>Ferroelectrics</i> , <b>2006</b> , 340, 121-128	0.6	5
57	Surface potential properties on near-stoichiometric LiNbO3 crystals with nanoscale domain-engineered structures. <i>Journal of Electroceramics</i> , <b>2006</b> , 16, 399-402	1.5	5
56	Structural developments during heating in LiNbO3 precursors synthesized by the sol-gel method. Journal of Materials Science, <b>1995</b> , 30, 1993-1998	4.3	5
55	Neuromorphic transistor achieved by redox reaction of WO3thin film. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 04FK01	1.4	4
54	Oxide ion and proton conduction controlled in nano-grained yttria stabilized ZrO2 thin films prepared by pulse laser deposition. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SDDG01	1.4	4
53	Tbit/Inch 2 Data Storage Using Scanning Nonlinear Dielectric Microscopy. Ferroelectrics, 2003, 292, 51-	<b>58</b> 5.6	4
52	A Voltage-Controlled Oscillator Using Variable Capacitors with a Thin Dielectric Electrolyte Film. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 2788-2797	4	4
51	Quantum conductance in memristive devices: fundamentals, developments, and applications <i>Advanced Materials</i> , <b>2022</b> , e2201248	24	4
50	Atomic Switches <b>2016</b> , 515-546		3
49	Effect of sintering conditions on mixed ionic-electronic conducting properties of silver sulfide nanoparticles. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 053530	2.5	3
48	Transmission electron microscopy study on epitaxial growth behaviors of sol-gel-derived LiNbO3 films. <i>Journal of Crystal Growth</i> , <b>1997</b> , 179, 577-584	1.6	3
47	Effect of subgrain boundaries on domain-inverted structure in periodically poled near-stoichiometric LiTaO3 crystal. <i>Optical Materials</i> , <b>2008</b> , 31, 276-279	3.3	3
46	Fabrication of microdomains at the +Z surface of near-stoichiometric lithium tantalate crystals. Journal Physics D: Applied Physics, <b>2006</b> , 39, 3103-3106	3	3
45	Domain And Surface Engineering Of Ferroelectric Crystal LiNbO3 For Novel Devices. <i>Materials Technology</i> , <b>2004</b> , 19, 162-167	2.1	3
44	Domain patterns on ferroelectric Rh:BaTiO3 single crystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2005</b> , 120, 137-140	3.1	3
43	Atomic Switch-Nano Device using the Transfer of Atoms(Ions) <i>Hyomen Kagaku</i> , <b>2006</b> , 27, 232-238		3
42	A Variety of Functional Devices Realized by Ionic Nanoarchitectonics, Complementing Electronics Components. <i>Advanced Electronic Materials</i> ,2100645	6.4	3
41	Neuromorphic System for Edge Information Encoding: Emulating Retinal Center-Surround Antagonism by Li-Ion-Mediated Highly Interactive Devices. <i>Nano Letters</i> , <b>2021</b> , 21, 7938-7945	11.5	3

40	A mesoporous SiO2 thin films-based ionic decision-maker for solving multi-armed bandit problems. Japanese Journal of Applied Physics, <b>2020</b> , 59, SIIG01	1.4	2
39	Oxygen-tolerant operation of all-solid-state ionic-gating devices: advantage of all-solid-state structure for ionic-gating. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SIIG09	1.4	2
38	A graphene oxide-based ionic decision-maker for simple fabrication and stable operation. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SIIG03	1.4	2
37	Unexpected metal-insulator transition in thick Ca1-xSrxVO3 film on SrTiO3 (100) single crystal. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 133106	3.4	2
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